

## LG Innotek Co., Ltd.

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## **Description of change**

FCC ID: YZP-VL1000 Base Model: LTD-VL1000

Variation Model: LTD-VL1110, LTD-VL1200

I inform that modules of between above models has minor change.

The differences between LTD-VL1000 and LTD-VL1110 are momory and changed resisters in below table.

LTD-VL1110	LTD-VL1000	Description of changes
S34MS02G200BHI00 (SPANSION, 2G NAND)	S34MS01G200BHI00 (SPANSION, 1G NAND)	Memory change (1G→2G)
RESOLUTION   RET	### CF1	Add the Pull-up resister (R511) for stabilization of the NAND memory.
Removed the R507	DNI	For System stabilization

The difference between LTD-VL1000 and LTD-VL1200 is changed resisters in below table.

LTD-VL1200	LTD-VL1000	Description of changes
	REG_NP_N   D   REG_NP_N   D	Add the Pull-up resister (R511) for stabilization of the NAND memory.
Removed R507	VCC Set ORD ORD ORD ORD ORD	For System stabilization

Exclude above description of changes, other part is same between LTD-VL1000 and LTD-VL1110, LTD-VL1200.

Sincerely,

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